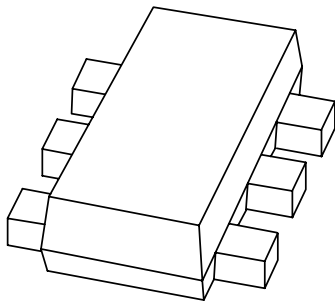


DATA SHEET



PBSS2515VS

15 V low $V_{CE(sat)}$ NPN double transistor

Product data sheet
Supersedes data of 2001 Nov 07

2004 Dec 23

15 V low $V_{CE(sat)}$ NPN double transistor**PBSS2515VS****FEATURES**

- 300 mW total power dissipation
- Very small 1.6×1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Low collector-emitter saturation voltage
- High current capability
- Improved thermal behaviour due to flat lead
- Replaces two SC-75/SC-89 packaged low V_{CEsat} transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} double transistor in a SOT666 plastic package.

PNP complement: PBSS3515VS.

MARKING

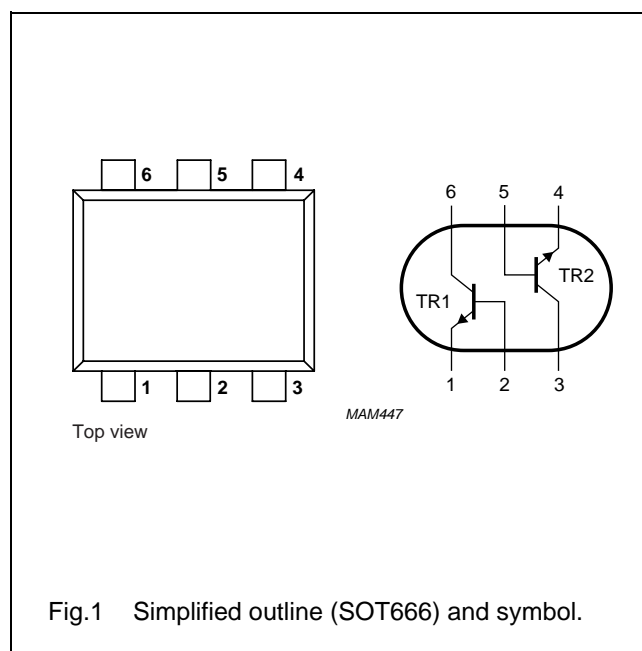
TYPE NUMBER	MARKING CODE
PBSS2515VS	N9

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	15	V
I_{CM}	peak collector current	1	A
R_{CEsat}	equivalent on-resistance	<500	m Ω

PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2

**ORDERING INFORMATION**

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS2515VS	—	plastic surface mounted package; 6 leads	SOT666

15 V low $V_{CE(sat)}$ NPN double transistor

PBSS2515VS

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor unless otherwise specified					
V_{CBO}	collector-base voltage	open emitter	–	15	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	500	mA
I_{CM}	peak collector current		–	1	A
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

15 V low $V_{CE(sat)}$ NPN double transistor

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

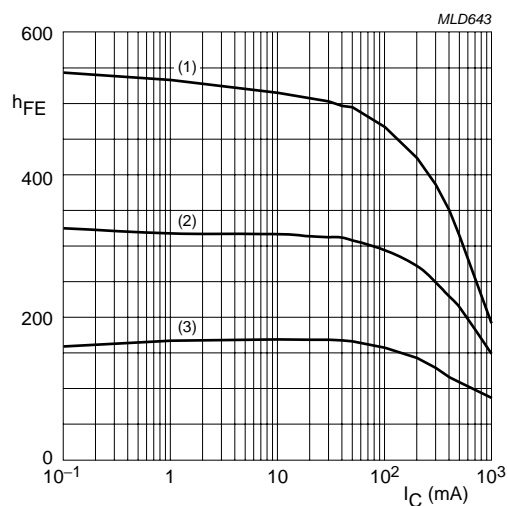
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor unless otherwise specified						
I_{CBO}	collector-base cut-off current	$V_{CB} = 15\text{ V}; I_E = 0\text{ A}$	–	–	100	nA
		$V_{CB} = 15\text{ V}; I_E = 0\text{ A}; T_J = 150\text{ }^{\circ}\text{C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	150	–	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; \text{note 1}$	90	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	25	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA}$	–	–	150	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	250	mV
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	300	<500	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	1.1	V
V_{BE}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	–	–	0.9	V
f_T	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	250	420	–	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	–	4.4	6	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

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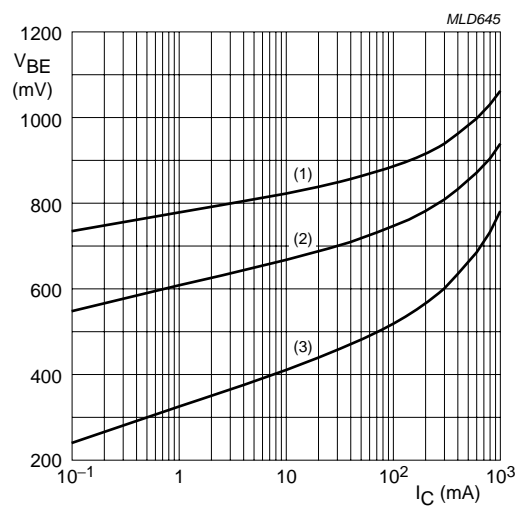
$V_{CE} = 2 \text{ V.}$

(1) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$

(3) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

Fig.2 DC current gain as a function of collector current; typical values.



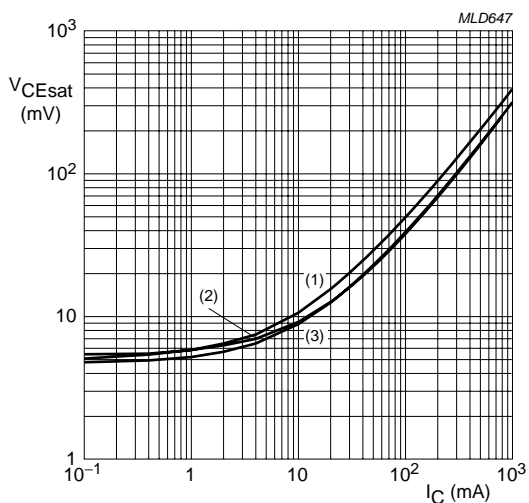
$V_{CE} = 2 \text{ V.}$

(1) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$

(3) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$

Fig.3 Base-emitter voltage as a function of collector current; typical values.



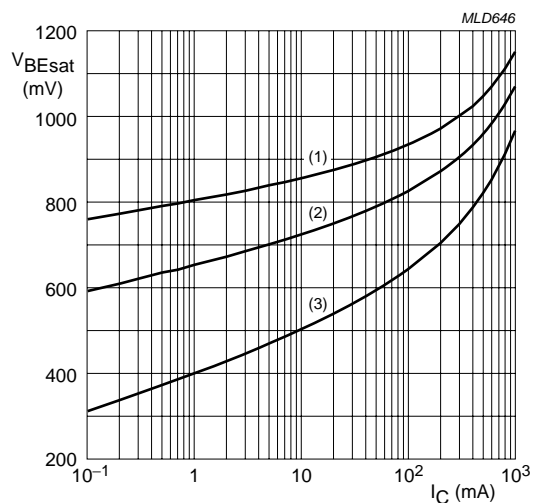
$I_C/I_B = 20.$

(1) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$

(2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$

(3) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 20.$

(1) $T_{amb} = 150 \text{ }^{\circ}\text{C.}$

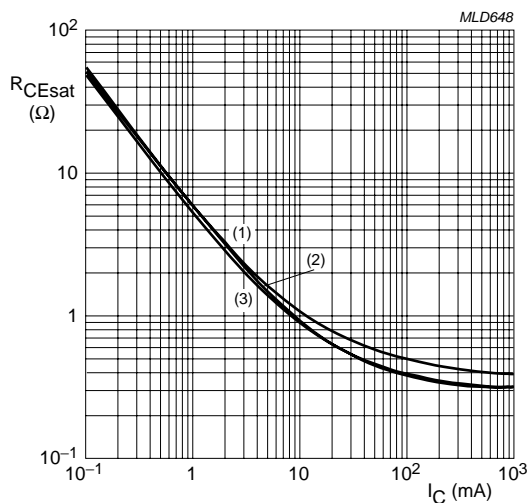
(2) $T_{amb} = 25 \text{ }^{\circ}\text{C.}$

(3) $T_{amb} = -55 \text{ }^{\circ}\text{C.}$

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

15 V low $V_{CE(sat)}$ NPN double transistor

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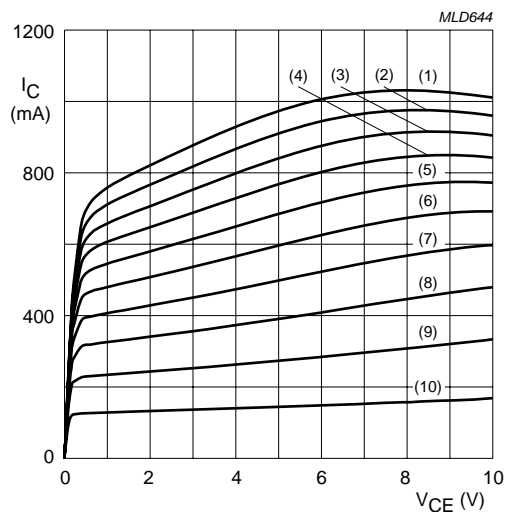
$I_C/I_B = 20$.

(1) $T_{amb} = 150\text{ °C}$.

(2) $T_{amb} = 25\text{ °C}$.

(3) $T_{amb} = -55\text{ °C}$.

Fig.6 Equivalent on-resistance as a function of collector current; typical values.



$T_{amb} = 25\text{ °C}$.

(1) $I_B = 4.6\text{ mA}$.

(6) $I_B = 2.3\text{ mA}$.

(2) $I_B = 4.14\text{ mA}$.

(7) $I_B = 1.84\text{ mA}$.

(3) $I_B = 3.68\text{ mA}$.

(8) $I_B = 1.38\text{ mA}$.

(4) $I_B = 3.22\text{ mA}$.

(9) $I_B = 0.92\text{ mA}$.

(5) $I_B = 2.76\text{ mA}$.

(10) $I_B = 0.46\text{ mA}$.

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

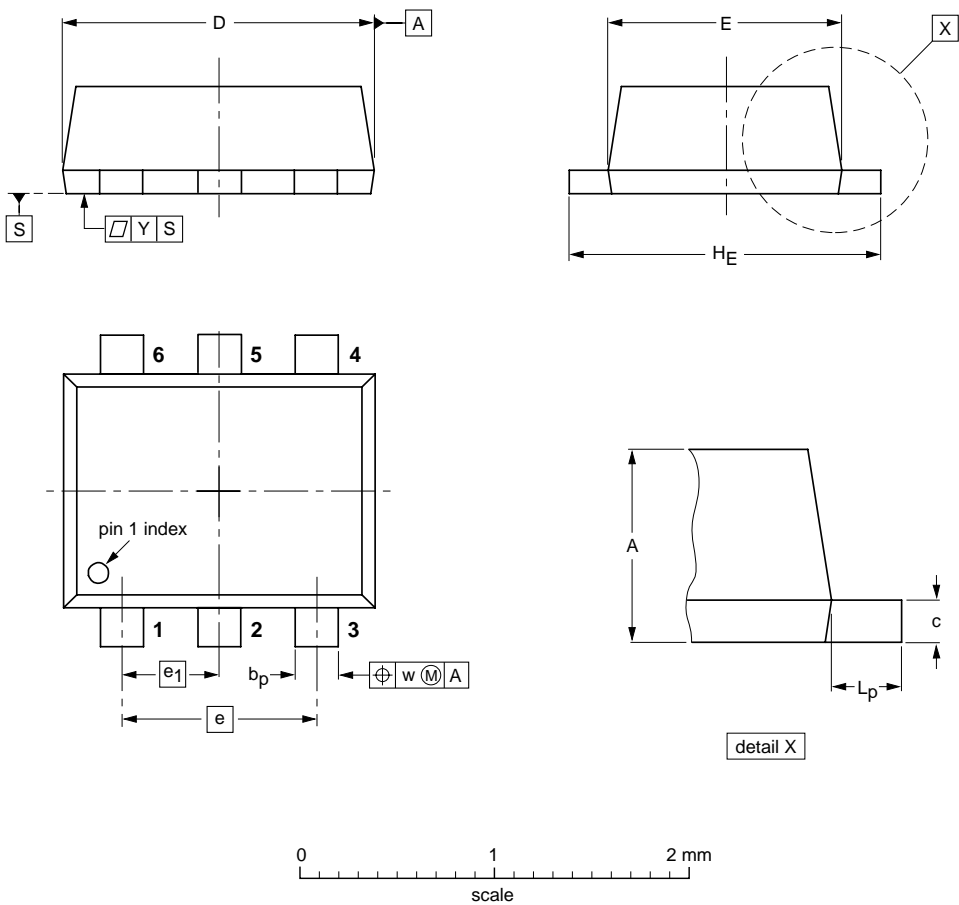
15 V low $V_{CE(sat)}$ NPN double transistor

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PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT666						04-11-08 06-03-16

15 V low $V_{CE(sat)}$ NPN double transistor

PBSS2515VS

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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Printed in The Netherlands

R75/03/pp9

Date of release: 2004 Dec 23

Document order number: 9397 750 14426

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